set the high pass filter at a first voltage level such that the detector detects the scattered electrons with the high pass filter while set at the first voltage level, the high pass filter detecting a first electron intensity level of the scattered electrons that is used to generate a first image of the inspected region;

set the high pass filter at a second voltage level such that the detector detects the scattered electrons with the high pass filter while set at the second voltage level, the high pass filter detecting a second electron intensity level of the scattered electrons that is used to generate a second image of the inspected region;

determine a first differential electron intensity level, which is the difference between the first electron intensity level and the second electron intensity level, wherein the first differential electron intensity level is the electron intensity level in an energy window between the first and second voltage level; and

generate a first resulting image of the inspected region from the differential electron intensity level.

Please **ADD** the following new claims:

22. (New) A method as recited in claim 1, wherein the electron intensity level corresponds to the measured number of scattered electrons.

23. (New) A method as recited in claim 1, wherein the first and second voltage levels are predetermined.

REMARKS

In the Office Action, the Examiner states that the Applicant has not complied with one or more conditions for receiving the benefit of an earlier filing date under 35 U.S.C. 119(e); rejects claims 1-6, 10-12, and 17-21 under 35 U.S.C. 102(b) as being anticipated by Iwasaki (U.S. 4,983,830); and rejects claims 7-9 and 13-16 under 35 U.S.C. 103(a) as being unpatentable over Iwasaki and further in view of Lo et al. (U.S. 6,344,750). The rejections are fully traversed below. Reconsideration of the application is respectfully requested based on the following remarks.

New claims 22 and 23 have been added. Accordingly, claims 1-23 are now pending in this application.